

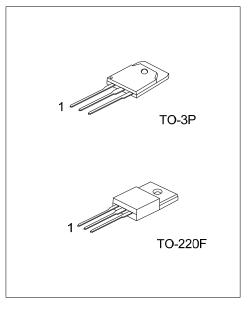
MJE13011

NPN EPITAXIAL SILICON TRANSISTOR

HIGH VOLTAGE HIGH SPEED SWITCHING

FEATURES

- * High voltage, high speed switching
- * High reliability



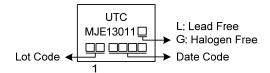
ORDERING INFORMATION

Ordering Number		Deekege	Pin Assignment			Decking	
Lead Free	Halogen Free	Package	1	2	3	Packing	
MJE13011L-TF3-T	MJE13011G-TF3-T	TO-220F	В	С	Е	Tube	
MJE13011L-T3P-T	MJE13011G-T3P-T	TO-3P	В	С	Е	Tube	
Noto: Din Assignment: A: An	ada K: Cathada	·					

Note: Pin Assignment: A: Anode K: Cathode

MJE13011G-TF3-T	(1)Packing Type	(1) T: Tube
	(2)Package Type	(2) TF3: TO-220F, T3P: TO-3P
	(3)Green Package	(3) G: Halogen Free and Lead Free, L: Lead Free

MARKING



■ ABSOLUTE MAXIMUM RATINGS (T_c=25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Collector Base Voltage		V _{CBO}	450	V
Collector Emitter Voltage		V _{CEO}	400	V
		V _{CEO(SUS)}	400	V
Emitter Base Voltage		V _{EBO}	7	V
Collector Current		Ιc	10	А
Base Current		I _B	3	А
Power Dissipation	TO-220F	- P _D -	36	W
	TO-3P		195	W
Junction Temperature		ТJ	+150	°C
Storage Temperature		T _{STG}	-40 ~ +150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

THERMAL DATA

PARAMETER		SYMBOL	RATINGS	UNIT
Thermal Resistance Junction to	TO-220F	0	3.47	°C/W
Case	TO-3P	θ ^{ıc}	0.64	°C/W

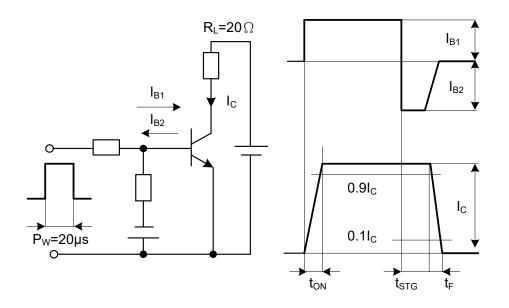
■ ELECTRICAL SPECIFICATIONS (T_c=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector Base Voltage	V_{CBO}	I _{CBO} =1mA	450			V
Collector Emitter Voltage	V_{CEO}	I _{CEO} =10mA	400			V
Collector Emitter Voltage	V _{CEO (SUS)}	I _C =1A	400			V
Emitter Base Voltage	V_{EBO}	I _{EBO} =0.1mA	7			V
Collector-Emitter Saturation Voltage	V _{CE (SAT)}				1.2	V
Base Emitter Saturation Voltage	V _{BE (SAT)}	I _C =4A, I _B =0.8A			1.5	V
Collector Cut-off Current	I _{CBO}	V _{CBO} =450V			1.0	mA
Emitter Cut-off Current	I _{EBO}	V _{EBO} =7V			0.1	mA
DC Current Gain	h _{FE}	I_{C} =4A, V_{CE} =5V	10		40	
Switching Time	t _{on}				1.0	μs
	t _{stg}	I _C =7.5A, I _{B1} =-I _{B2} =1.5A R _L =20Ω, Pw=20µs, Duty ≤ 2%			2.0	μs
	t _F	$R_L = 2022$, $Fw = 20\mu S$, $Duly \le 2\%$			1.0	μs



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SWITCHING TIME TEST CIRCUIT

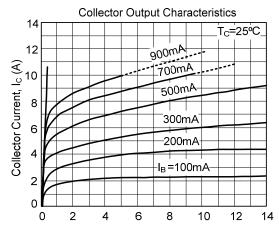




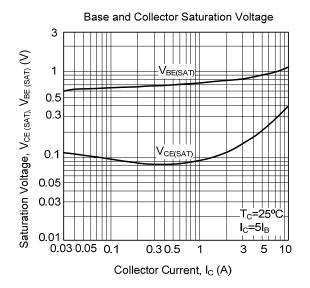
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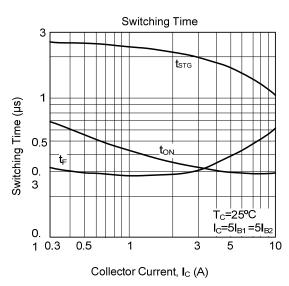
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TYPICAL CHARACTERISTICS

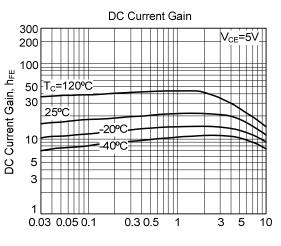


Collector Emitter Voltage, V_{CE} (V)

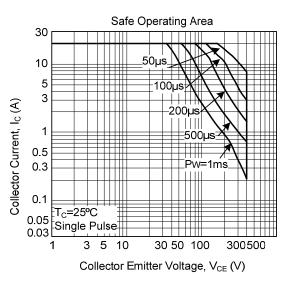








Collector Current, I_C (A)



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